SiA469DJ Vishay Siliconix

RoHS

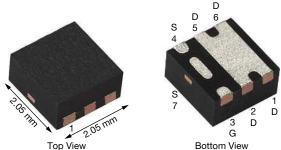
COMPLIANT

HALOGEN

www.vishay.com

P-Channel 30 V (D-S) MOSFET

PowerPAK[®] SC-70-6L Single



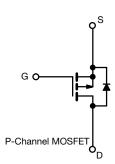
 $\begin{tabular}{|c|c|c|c|} \hline PRODUCT SUMMARY \\ \hline V_{DS} (V) & -30 \\ \hline R_{DS(on)} max. (\Omega) at V_{GS} = -10 V & 0.0265 \\ \hline R_{DS(on)} max. (\Omega) at V_{GS} = -4.5 V & 0.0400 \\ \hline Q_g typ. (nC) & 10 \\ \hline I_D (A) ^a & -12 \\ \hline Configuration & Single \\ \hline \end{tabular}$

FEATURES

- TrenchFET[®] Gen III p-channel power MOSFET
- Thermally enhanced PowerPAK[®] SC-70 package
- 100% R_q tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load switch
- DC/DC converters
- · High speed switching
- Power management in battery-operated, mobile and wearable devices



ORDERING INFORMATION	
Package	PowerPAK SC-70
Lead (Pb)-free and halogen-free	SiA469DJ-T1-GE3

ABSOLUTE MAXIMUM RATING			,	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-30	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current (T _J = 150 °C)	T _C = 25 °C		-12 ^a	
	T _C = 70 °C	1 . 🗆	-12 ^a	
	T _A =25 °C		-8.8 ^{b, c}	
	T _A = 70 °C	1	_7 b, c	А
Pulsed drain current (t = 100 µs)		I _{DM}	-40	
Continuous source-drain diode current	T _C = 25 °C		-12 ^a	
	T _A = 70 °C	I _S	-2.7 ^{b, c}	
Maximum power dissipation	T _C = 25 °C		15.6	
	T _C = 70 °C		10	
	T _A = 25 °C	P _D	3.3 ^{b, c}	W
	T _A = 70 °C	1	2.1 ^{b, c}	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	*0
Soldering recommendations (peak temperature) d, e			260	°C

THERMAL RESISTANCE RATINGS

I RENMAL RESISTANCE RATINGS							
PARAMETER		SYMBOL TYPICAL		MAXIMUM	UNIT		
Maximum junction-to-ambient ^{b, f}	t ≤ 5 s	R _{thJA}	30	38	°C/W		
Maximum junction-to-case (drain)	Steady state	R _{thJC}	6.5	8	C/W		

Notes

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. See solder profile (<u>www.vishay.com/ppg?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 80 °C/W.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static			•		•		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	-30	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050 A	-	-25.5	-		
V _{GS(th)} temperature coefficient	$\Delta V_{GS(th)}/T_J$	I _D = -250 μΑ	-	7	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	-1	-	-3	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$	-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS} -	$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1	— μΑ	
		$V_{DS} = -30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$	-	-	-10		
On-state drain current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-10	-	-	А	
Drain-source on-state resistance ^a	_	$V_{GS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	0.0210	0.0265	Ω	
	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -3 \text{ A}$	-	0.0300	0.0400		
Forward transconductance ^a	g _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	15	-	S	
Dynamic ^b			•		•		
Input capacitance	C _{iss}		-	1020	-	pF	
Output capacitance	C _{oss}	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$	-	130	-		
Reverse transfer capacitance	C _{rss}		-	115	-		
-	0	V_{DS} = -15 V, V_{GS} = -10 V, I_{D} = -5 A	-	21	32	nC	
Total gate charge	Qg	$V_{DS} = -15 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -5 \text{ A}$	-	10	15		
Gate-source charge	Q _{gs}		-	2.3	-		
Gate-drain charge	Q _{gd}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$	-	3.6	-		
Gate resistance	Rg	f = 1 MHz	1.8	9	18	Ω	
Turn-on delay time	t _{d(on)}		-	30	60	- ns	
Rise time	t _r	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = -15 \; V, \; R_{\text{L}} = 3 \; \Omega, \; I_{\text{D}} \cong -5 \; A, \\ V_{\text{GEN}} = -4.5 \; V, \; R_{\text{g}} = 1 \; \Omega \end{array}$	-	26	50		
Turn-off delay time	t _{d(off)}		-	25	50		
Fall time	t _f		-	14	30		
Turn-on delay time	t _{d(on)}		-	7	15		
Rise time	t _r	$V_{DD} = -15 \text{ V}, \text{ R}_{\text{L}} = 3 \Omega, \text{ I}_{D} \cong -5 \text{ A},$	-	17	35		
Turn-off delay time	t _{d(off)}	$V_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$	-	30	30		
Fall time	t _f		-	15	30		
Drain-Source Body Diode Characterist	ics		•				
Continuous source-drain diode current	IS	T _C = 25 °C	-	-	-12		
Pulse diode forward current	I _{SM}	-		-	-40	A	
Body diode voltage	V _{SD}	$I_{\rm S}$ = -5 A, $V_{\rm GS}$ = 0 V	-	-0.85	-1.2	V	
Body diode reverse recovery time	t _{rr}		-	18	40	ns	
Body diode reverse recovery charge	Q _{rr}		-	10	20	nC	
Reverse recovery fall time	t _a	$I_F = -5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 ^\circ\text{C}$	-	10	-		
Reverse recovery rise time	t _b		-	8	-	ns	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

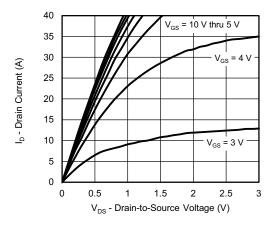
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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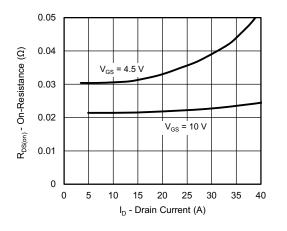


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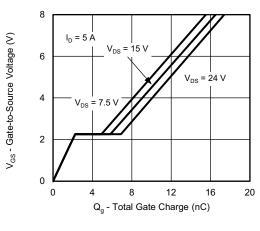
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



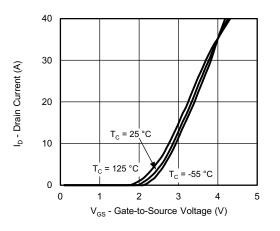
Output Characteristics



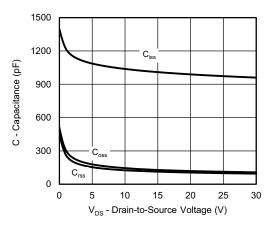
On-Resistance vs. Drain Current and Gate Voltage



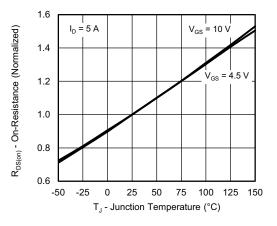
Gate Charge



Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

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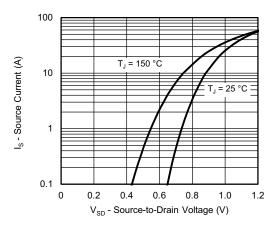
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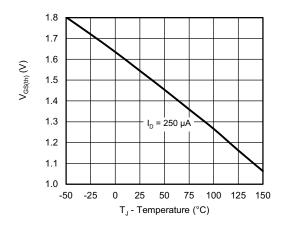


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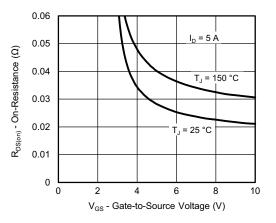
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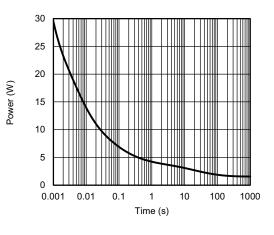
Source-Drain Diode Forward Voltage



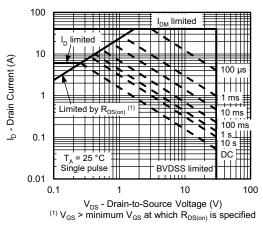
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

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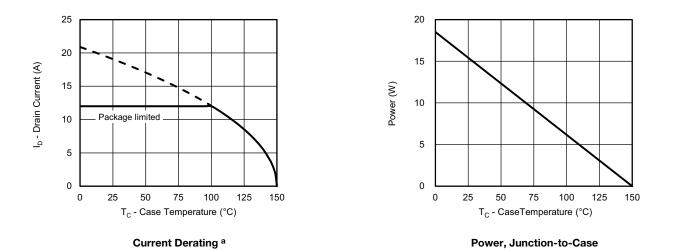
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Note

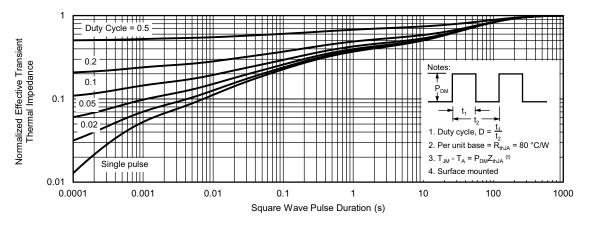
a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



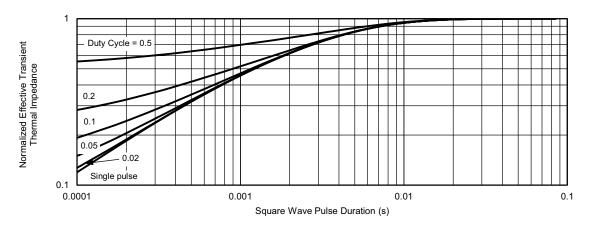
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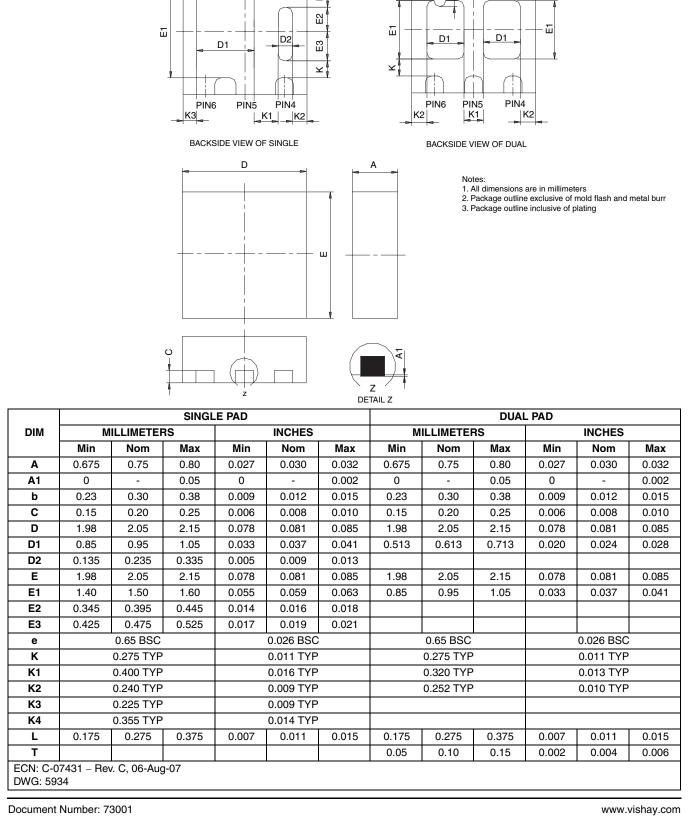


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?75354.



PowerPAK[®] SC70-6L

b PIN2 PIN1 PIN3 _ ₹

Package Information Vishay Siliconix

_ ₿

b

PIN3

PIN2

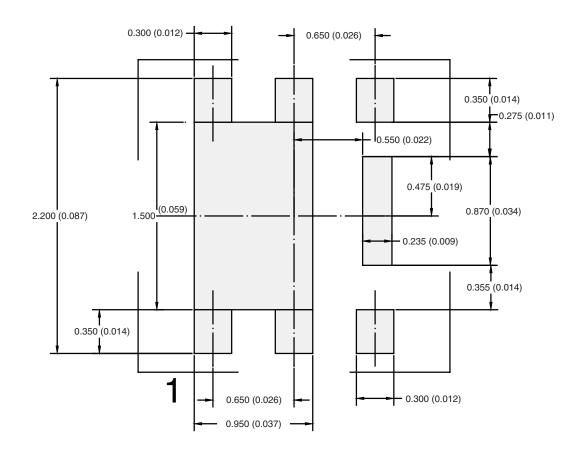
PIN1

¥

VISHA



RECOMMENDED PAD LAYOUT FOR PowerPAK[®] SC70-6L Single



Dimensions in mm/(Inches)

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